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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Schottky Diode Gen²

 $V_{RRM} = 100 V$ $I_{FAV} = 2x 25 A$ $V_{F} = 0.72 V$

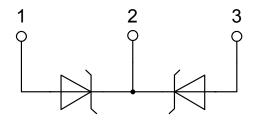
High Performance Schottky Diode Low Loss and Soft Recovery Common Cathode

Part number

DSA50C100QB



Backside: cathode



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-3P

- Industry standard outline compatible with TO-247
- RoHS compliant
- Epoxy meets UL 94V-0

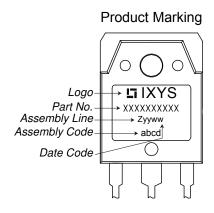




Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			100	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			100	V
I _R	reverse current, drain current	V _R = 100 V	$T_{VJ} = 25^{\circ}C$			450	μΑ
		$V_R = 100 V$	$T_{VJ} = 125^{\circ}C$			5	mΑ
V _F	forward voltage drop	I _F = 25 A	$T_{VJ} = 25^{\circ}C$			0.90	V
		$I_F = 50 A$				1.07	V
		I _F = 25 A	T _{VJ} = 125°C			0.72	V
		$I_F = 50 A$				0.90	V
I _{FAV}	average forward current	T _c = 155°C	T _{vJ} = 175°C			25	Α
		rectangular d = 0.5					i I I I
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.45	V
r _F	slope resistance	ess calculation only				7.3	mΩ
R _{thJC}	thermal resistance junction to case	9				0.95	K/W
R _{thCH}	thermal resistance case to heatsing	k			0.25		K/W
P _{tot}	total power dissipation		$T_{c} = 25^{\circ}C$			160	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			440	Α
C¹	junction capacitance	V _R = 12 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		289		pF



Package TO-3P				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal 1)			50	Α	
T _{VJ}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				5		g	
M _D	mounting torque		0.8		1.2	Nm	
F _c	mounting force with clip		20		120	N	



Part number

D = Diode

S = Schottky Diode

A = low VF

50 = Current Rating [A]

C = Common Cathode

100 = Reverse Voltage [V] QB = TO-3P (3)

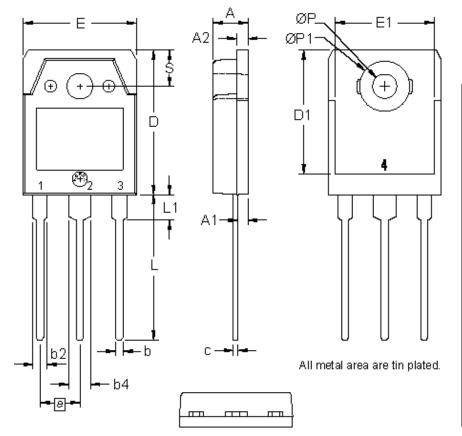
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA50C100QB	DSA50C100QB	Tube	30	504033

Similar Part	Package	Voltage class
DSA50C100HB	TO-247AD (3)	100
DSA60C100PB	TO-220AB (3)	100

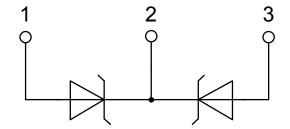
Equiva	alent Circuits for	Simulation	* on die level	T _{VJ} = 175 °C
$I \rightarrow V_0$	R_0	Schottky		
V _{0 max}	threshold voltage	0.45		V
R _{0 max}	slope resistance *	4.7		$m\Omega$



Outlines TO-3P



Dim.	Millir	neter	Inc	hes
Dirri.	min	max	min	max
Α	4.70	4.90	0.185	0.193
A1	1.30	1.50	0.051	0.059
A2	1.45	1.65	0.057	0.065
b	0.90	1.15	0.035	0.045
b2	1.90	2.20	0.075	0.087
b4	2.90	3.20	0.114	0.126
0	0.55	0.80	0.022	0.031
О	19.80	20.10	0.780	0.791
D1	16.90	17.20	0.665	0.677
Е	15.50	15.80	0.610	0.622
E1	13.50	13.70	0.531	0.539
е	5.45 BSC		0.215 BSC	
Г	19.80	20.20	0.780	0.795
L1	3.40	3.60	0.134	0.142
ØР	3.20	3.40	0.126	0.134
ØP1	6.90	7.10	0.272	0.280
S	4.90	5.10	0.193	0.201





Schottky

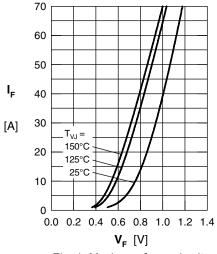


Fig. 1 Maximum forward voltage drop characteristics

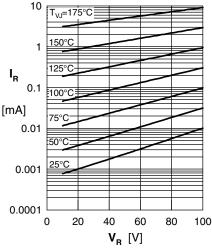


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

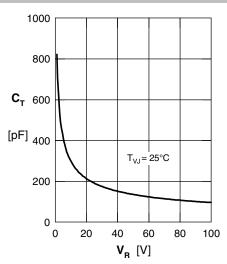


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

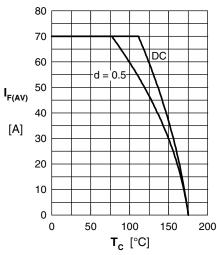


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_{C}

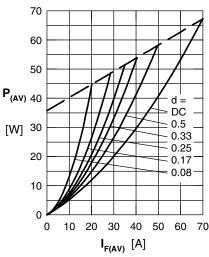


Fig. 5 Forward power loss characteristics

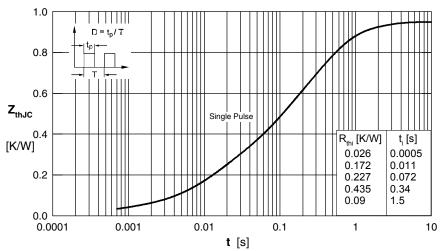


Fig. 6 Transient thermal impedance junction to case

Note: All curves are per diode